

L Number	Hits	Search Text	DB	Time stamp
1	100	LDMOS with CMOS	USPAT; US-PPGPUB	2003/10/14 14:05
2	41	(LDMOS with CMOS) same power	USPAT; US-PPGPUB	2003/10/14 14:06

L Number	Hits	Search Text	DB	Time stamp
-	262	(LDMOS or (lateral adj DMOS) or (lateral adj diffus\$3 adj mos)) and ("V.sub.th." or (threshold nearl voltage))	USPAT; US-PPGPUB	2003/07/28 17:51
-	93336	(HV with LV) or (low with high with voltage)	USPAT; US-PPGPUB	2003/07/28 17:47
-	26320	((HV with LV) or (low with high with voltage)) same (transistor or MOS)	USPAT; US-PPGPUB	2003/07/28 17:49
-	12576	((HV with LV) or (low with high with voltage)) same (transistor or MOS) and (threshold with voltage)	USPAT; US-PPGPUB	2003/07/28 17:49
-	10706	((((HV with LV) or (low with high with voltage)) same (transistor or MOS)) and (threshold with voltage)) not (adjustment)	USPAT; US-PPGPUB	2003/07/28 17:50
-	93	(((((HV with LV) or (low with high with voltage)) same (transistor or MOS)) and (threshold with voltage)) not (adjustment)) and ldmos	USPAT; US-PPGPUB	2003/07/28 17:50
-	4	(((((HV with LV) or (low with high with voltage)) same (transistor or MOS)) and (threshold with voltage)) not (adjustment)) and ldmos not ((LDMOS or (lateral adj DMOS) or (lateral adj diffus\$3 adj mos)) and ("V.sub.th." or (threshold nearl voltage)))	USPAT; US-PPGPUB	2003/07/28 17:50
-	103	((((HV with LV) or (low with high with voltage)) same (transistor or MOS)) and (threshold with voltage)) and ldmos	USPAT; US-PPGPUB	2003/07/28 17:50
-	6	(((((HV with LV) or (low with high with voltage)) same (transistor or MOS)) and (threshold with voltage)) and ldmos) not ((LDMOS or (lateral adj DMOS) or (lateral adj diffus\$3 adj mos)) and ("V.sub.th." or (threshold nearl voltage)))	USPAT; US-PPGPUB	2003/07/28 17:50
-	765	(LDMOS or (lateral adj DMOS) or (lateral adj diffus\$3 adj mos))	USPAT; US-PPGPUB	2003/07/28 17:51
-	503	((LDMOS or (lateral adj DMOS) or (lateral adj diffus\$3 adj mos))) not ((LDMOS or (lateral adj DMOS) or (lateral adj diffus\$3 adj mos)) and ("V.sub.th." or (threshold nearl voltage)))	USPAT; US-PPGPUB	2003/07/28 18:14
-	14	5264719.URPN.	USPAT	2003/07/28 17:54
-	5	("4626879" "4628341" "4811075" "4994889" "4994904").PN.	USPAT	2003/07/28 17:55
-	0	RE37424.URPN.	USPAT	2003/07/28 18:05
-	9	("4120707" "4628341" "4710241" "4887142" "4890142" "4918026" "4928164" "4962052" "5156989").PN.	USPAT	2003/07/28 18:05
-	29	4120707.URPN.	USPAT	2003/07/28 18:06
-	0	6451640.URPN.	USPAT	2003/07/28 18:10
-	11	("4628341" "4918026" "5043788" "5047358" "5254487" "5468666" "5527722" "5578855" "5747850" "5795803" "5847432").PN.	USPAT	2003/07/28 18:10
-	13	5847432.URPN.	USPAT	2003/07/28 18:12
-	1	"4866002".PN.	USPAT	2003/07/28 18:13
-	14	5043788.URPN.	USPAT	2003/07/28 18:13
-	3	("4258379" "4379726" "4894692").PN.	USPAT	2003/07/28 18:13
-	5	("5726477" "5852314" "5917222" "6258644" "6277682").PN.	USPAT	2003/07/28 18:18
-	4939	high with low with (voltage or power) with (CMOS or MOSFET)	USPAT; US-PPGPUB	2003/07/29 10:25

-	740	(high with low with (voltage or power) with (CMOS or MOSFET)) and 438/\$.cccls.	USPAT; US-PPGPUB	2003/07/29 13:46
-	7	("4435896" "4535529" "4651406" "4753898" "5607868" "5712201" "5834352").PN.	USPAT	2003/07/29 11:23
-	5	6043128.URPN.	USPAT	2003/07/29 11:23
-	6	("4651406" "5243210" "5407849" "5966321" "5989949" "6043128").PN.	USPAT	2003/07/29 11:26
-	92651	LDMOS with (MISFET) or (EPROM or EEPROM or DRAM)	USPAT; US-PPGPUB	2003/07/29 16:02
-	24	(LDMOS with (EPROM or EEPROM or DRAM))	USPAT; US-PPGPUB	2003/07/29 16:41
-	1	("5296393").PN.	USPAT; US-PPGPUB	2003/07/29 17:27
-	3	(("20010005037") or ("6255207") or ("5814555")).PN.	USPAT; US-PPGPUB	2003/07/29 17:35
-	1	("5621241").PN.	USPAT; US-PPGPUB	2003/07/30 11:25
-	5	LDMOS with (low adj voltage adj CMOS)	USPAT; US-PPGPUB	2003/08/10 11:12
-	0	LDMOS with (low adj voltage adj MOS)	USPAT; US-PPGPUB	2003/08/10 11:13
-	0	(LDMOS with (low adj voltage adj transistor)) and CMOS	USPAT; US-PPGPUB	2003/08/10 11:14
-	44	(LDMOS with (low adj voltage)) and CMOS	USPAT; US-PPGPUB	2003/08/10 11:16
-	1	("5,242,841").PN.	USPAT; US-PPGPUB	2003/08/10 11:16